



**SOT-89-3L Plastic-Encapsulate Transistors**

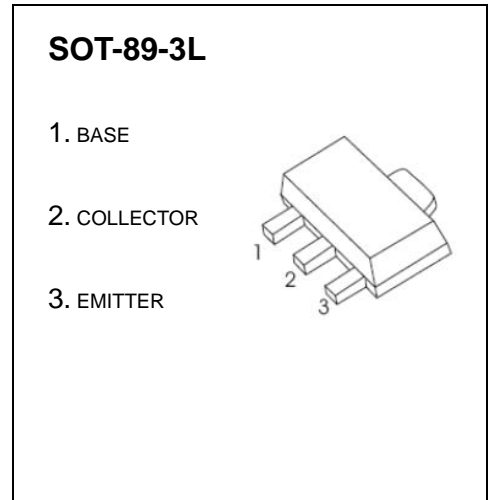
**2SA1797** TRANSISTOR (PNP)

**FEATURES**

- Low saturation voltage
- Excellent DC current gain characteristics
- Complements to 2SC4672

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-50	V
V <sub>CE0</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Continuous Collector Current	-2	A
I <sub>CM</sub>	Peak Pluse Current	-3	A
P <sub>C</sub>	Collector Power dissipation	500	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-50μA, I <sub>E</sub> =0	-50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-50μA, I <sub>C</sub> =0	-6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA	82		270	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-1A, I <sub>B</sub> =-50mA			-0.35	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A, f=100MHz		200		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		36		pF

**CLASSIFICATION OF h<sub>FE</sub>**

Rank	P	Q
Range	82-180	120-270
Marking	<b>AGP</b>	<b>AGQ</b>

# Typical Characteristics

# 2SA1797

